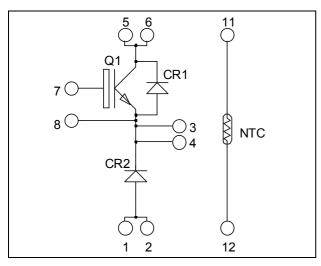
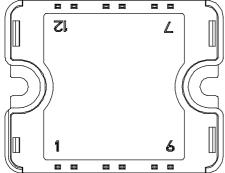


# Buck chopper NPT IGBT Power Module

$$V_{CES} = 600V$$
  
 $I_C = 90A$  @  $Tc = 80$ °C





Pins 1/2; 3/4; 5/6 must be shorted together

#### Application

- AC and DC motor control
- Switched Mode Power Supplies

#### **Features**

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
Ţ	Continuous Collector Current	$T_c = 25^{\circ}C$	110	
$I_{C}$	Continuous Conector Current	$T_c = 80$ °C	90	Α
$I_{CM}$	Pulsed Collector Current	$T_c = 25^{\circ}C$	315	1
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_c = 25^{\circ}C$	416	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150$ °C	200A @ 600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



### All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_i = 25^{\circ}C$			250	μA
$I_{CES}$	Zero Gate voltage Collector Current	$V_{CE} = 600V$	$T_{i} = 125^{\circ}C$			500	μΑ
* 7	Call of a Facility and a discarding Walter	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		2.0	2.5	V
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$I_C = 90A$	$T_j = 125$ °C		2.2		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1 \text{mA}$		3		5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20 \text{ V}, V_{CE} = 0 \text{ V}$				±150	nA

**Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			4300		pF
$C_{oes}$	Output Capacitance				470		
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			400		
$Q_{g}$	Total gate Charge	$V_{GE} = 15V$			330		
$Q_{ge}$	Gate – Emitter Charge	$V_{\text{Bus}} = 300\text{V}$			290		nC
$Q_{gc}$	Gate – Collector Charge	$I_C = 90A$			200		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			26		
$T_{\rm r}$	Rise Time	$V_{GE} = 15V$			25		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 400V$ $I_{\text{C}} = 90A$ $R_{\text{G}} = 5 \Omega$			150		ns
$T_{\mathrm{f}}$	Fall Time				30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_{C} = 90A$ $R_{G} = 5 \Omega$			26		ns
$T_{\rm r}$	Rise Time				25		
$T_{d(off)}$	Turn-off Delay Time				170		
$T_{\rm f}$	Fall Time				40		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$	$T_j = 125^{\circ}C$	_	4.3		I
$E_{\text{off}}$	Turn-off Switching Energy	$I_C = 90A$ $R_G = 5 \Omega$	$T_j = 125$ °C		3.5		mJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
T	Mayimayan Bayanga Laakaga Cymnant	V <sub>R</sub> =600V	$T_j = 25^{\circ}C$			100	۸
$I_{RM}$	Maximum Reverse Leakage Current	V R-000 V	$T_j = 125$ °C			500	μΑ
$I_{\mathrm{F}}$	DC Forward Current	$Tc = 80^{\circ}C$			100		A
	Diode Forward Voltage	$I_F = 100A$			1.6	2	
$V_{\mathrm{F}}$		$I_F = 200A$			2		V
		$I_F = 100A$	$T_{j} = 125^{\circ}C$		1.3		
t	Reverse Recovery Time	$I_F = 100A$ $V_R = 400V$	$T_j = 25$ °C		160		ns
$t_{\mathrm{rr}}$			$T_{j} = 125^{\circ}C$		220		113
Q <sub>rr</sub>	Reverse Recovery Charge	$\frac{V_R - 400 V}{\text{di/dt} = 200 \text{A/}\mu\text{s}}$	$T_j = 25$ °C		290		nC
			$T_{j} = 125^{\circ}C$		1530		IIC



### Thermal and package characteristics

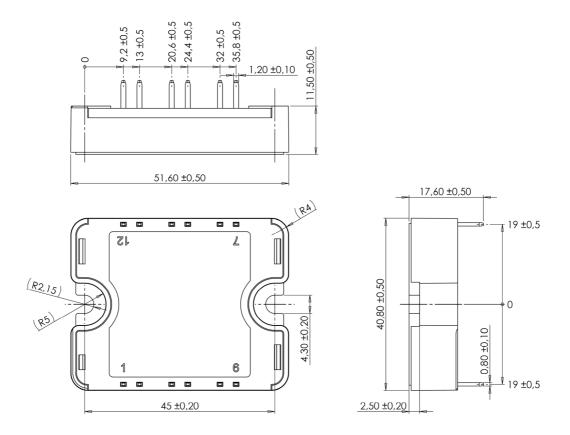
Symbol	Characteristic			Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance	IGBT			0.3	°C/W	
$R_{thJC}$		Diode			0.55	C/ VV	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range		-40		150		
$T_{STG}$	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight				80	g	

### Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature} \\ R_{T}: \text{ Thermistor value at T}$$

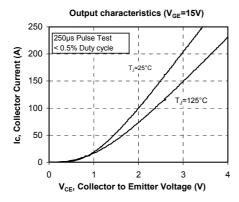
### SP1 Package outline (dimensions in mm)

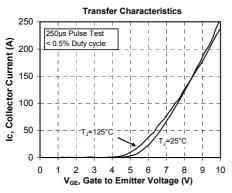


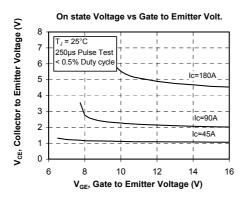
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

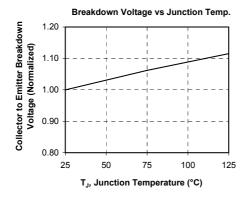


### **Typical Performance Curve**

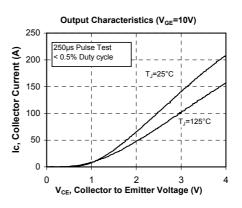


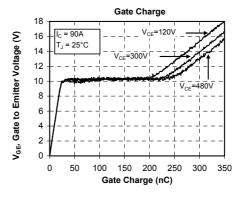


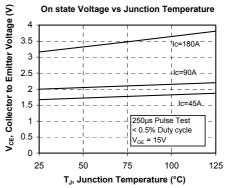


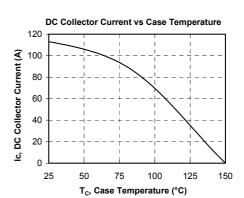


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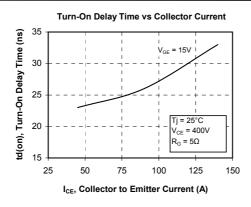


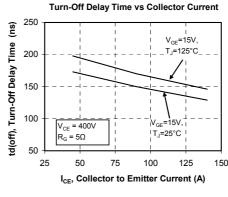


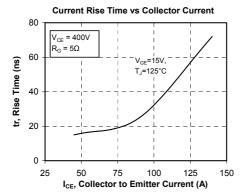


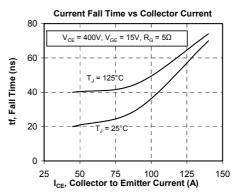


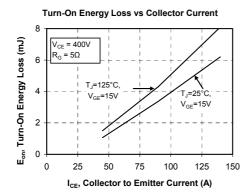


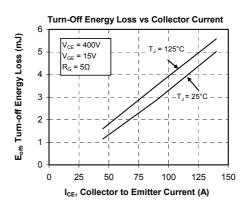


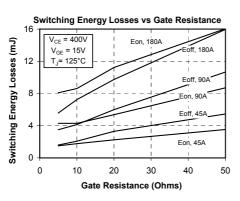


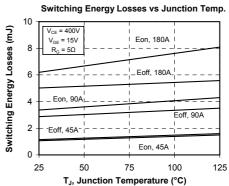




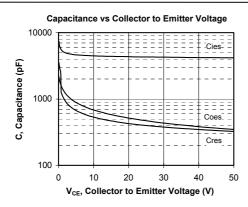


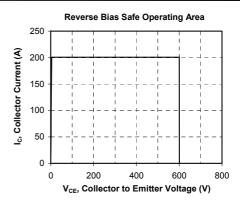




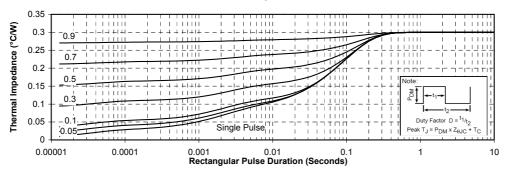


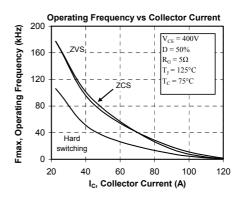






#### Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





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